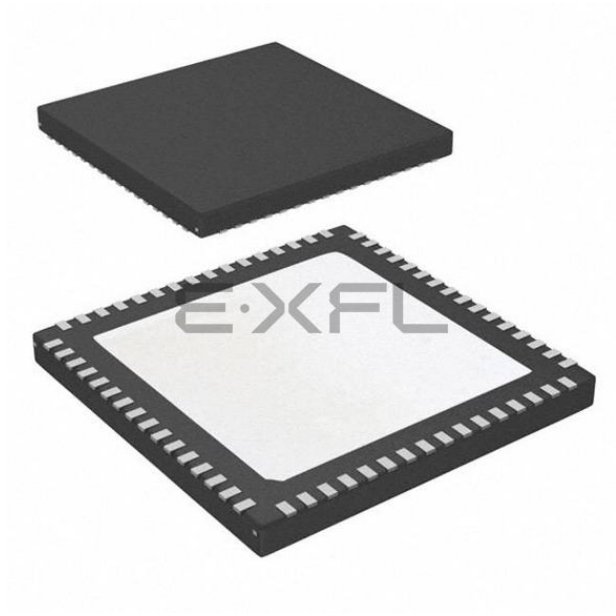

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Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 28x12b; D/A 2x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/sim3u166-b-gm

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 9[2,3]—Low Power Shutdown with VREG0 disabled, powered through VDD and VIO	I_{DD}	RTC Disabled, V_{DD} = 1.8 V, T_A = 25 °C	—	85	—	nA
		RTC w/ 16.4 kHz LFO, V_{DD} = 1.8 V, T_A = 25 °C	—	350	—	nA
		RTC w/ 32.768 kHz Crystal, V_{DD} = 1.8 V, T_A = 25 °C	—	620	—	nA
		RTC Disabled, V_{DD} = 3.0 V, T_A = 25 °C	—	145	—	nA
		RTC w/ 16.4 kHz LFO, V_{DD} = 3.0 V, T_A = 25 °C	—	500	—	nA
		RTC w/ 32.768 kHz Crystal, V_{DD} = 3.0 V, T_A = 25 °C	—	800	—	nA
Power Mode 9[2,3]—Low Power Shutdown with VREG0 in low-power mode, VDD and VIO powered through VREG0 (Includes VREG0 current)	I_{VREGIN}	RTC Disabled, VREGIN = 5 V, T_A = 25 °C	—	300	—	nA
		RTC w/ 16.4 kHz LFO, VREGIN = 5 V, T_A = 25 °C	—	650	—	nA
		RTC w/ 32.768 kHz Crystal, VREGIN = 5 V, T_A = 25 °C	—	950	—	nA
VIOHD Current (High-drive I/O disabled)	I_{VIOHD}	HV Mode (default)	—	2.5	5	µA
		LV Mode	—	2	—	nA

Notes:

1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Oscillator (EXTOSC0)[8]	I_{EXTOSC}	FREQCN = 111	—	3.8	4.7	mA
		FREQCN = 110	—	840	950	µA
		FREQCN = 101	—	185	220	µA
		FREQCN = 100	—	65	80	µA
		FREQCN = 011	—	25	30	µA
		FREQCN = 010	—	10	15	µA
		FREQCN = 001	—	5	10	µA
		FREQCN = 000	—	3	8	µA
SARADC0, SARADC1	I_{SARADC}	Sampling at 1 Msps, highest power mode settings.	—	1.2	1.5	mA
		Sampling at 250 ksps, lowest power mode settings.	—	390	510	µA
Temperature Sensor	I_{TSENSE}		—	75	105	µA
Internal SAR Reference	I_{REFFS}	Normal Power Mode	—	680	750	µA
		Low Power Mode	—	160	190	µA
VREF0	I_{REFP}		—	75	100	µA
Comparator 0 (CMP0), Comparator 1 (CMP1)	I_{CMP}	CMPMD = 11	—	0.5	—	µA
		CMPMD = 10	—	3	—	µA
		CMPMD = 01	—	10	—	µA
		CMPMD = 00	—	25	—	µA
Capacitive Sensing (CAPSENSE0)	I_{CS}	Continuous Conversions	—	55	80	µA
IDAC0[7], IDAC1[7]	I_{IDAC}		—	75	90	µA
IVC0[7]	I_{IVC}	I_{IN} = 0	—	1.5	2.5	µA
Voltage Supply Monitor (VMON0)	I_{VMON}		—	15	25	µA

Notes:

1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.4. Reset and Supply Monitor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
V_{DD} High Supply Monitor Threshold (VDDHITHEN = 1)	V_{VDDMH}	Early Warning	2.10	2.20	2.30	V
		Reset	1.95	2.05	2.1	V
V_{DD} Low Supply Monitor Threshold (VDDHITHEN = 0)	V_{VDDML}	Early Warning	1.81	1.85	1.88	V
		Reset	1.70	1.74	1.77	V
V_{REGIN} Supply Monitor Threshold	V_{VREGM}	Early Warning	4.2	4.4	4.6	V
Power-On Reset (POR) Threshold	V_{POR}	Rising Voltage on V_{DD}	—	1.4	—	V
		Falling Voltage on V_{DD}	0.8	1	1.3	V
V_{DD} Ramp Time	t_{RMP}	Time to $V_{DD} \geq 1.8$ V	10	—	3000	µs
Reset Delay from POR	t_{POR}	Relative to $V_{DD} \geq V_{POR}$	3	—	100	ms
Reset Delay from non-POR source	t_{RST}	Time between release of reset source and code execution	—	10	—	µs
$\overline{\text{RESET}}$ Low Time to Generate Reset	t_{RSTL}		50	—	—	ns
Missing Clock Detector Response Time (final rising edge to reset)	t_{MCD}	$F_{AHB} > 1$ MHz	—	0.4	1	ms
Missing Clock Detector Trigger Frequency	F_{MCD}		—	7.5	13	kHz
V_{DD} Supply Monitor Turn-On Time	t_{MON}		—	2	—	µs

Table 3.5. On-Chip Regulators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
3.3 V Regulator Characteristics (VREG0, Supplied from VREGIN Pin)						
Output Voltage (at VDD pin)	V_{DDOUT}	$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = 0	3.15	3.3	3.4	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = 1	3.15	3.3	3.4	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X I_{DDOUT} = 500 µA	2.3	2.8	3.6	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X I_{DDOUT} = 5 mA	2.1	2.65	3.3	V
Output Current (at VDD pin)*	I_{DDOUT}	$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = X	—	—	150	mA
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X	—	—	5	mA
Output Load Regulation	V_{DDLR}	BGDIS = 0	—	0.1	1	mV/mA
Output Capacitance	C_{VDD}		1	—	10	µF

***Note:** Total current VREG0 is capable of providing. Any current consumed by the SiM3C1xx reduces the current available to external devices powered from VDD.

Table 3.7. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Write Time[1]	t_{WRITE}	One 16-bit Half Word	20	21	22	µs
Erase Time[1]	t_{ERASE}	One Page	20	21	22	ms
	t_{ERALL}	Full Device	20	21	22	ms
V_{DD} Voltage During Programming	V_{PROG}		1.8	—	3.6	V
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles
Retention[2]	t_{RET}	T_A = 25 °C, 1k Cycles	10	100	—	Years

Notes:
1. Does not include sequencing time before and after the write/erase operation, which may take up to 35 µs. During a sequential write operation, this extra time is only taken prior to the first write and after the last write.
2. Additional Data Retention Information is published in the Quarterly Quality and Reliability Report.

Table 3.8. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Phase-Locked Loop (PLL0OSC)						
Calibrated Output Frequency*	$f_{PLL0OSC}$	Full Temperature and Supply Range	77	79	80	MHz
Power Supply Sensitivity*	$PSS_{PLL0OSC}$	T_A = 25 °C, Fout = 79 MHz	—	430	—	ppm/V
Temperature Sensitivity*	$TS_{PLL0OSC}$	V_{DD} = 3.3 V, Fout = 79 MHz	—	95	—	ppm/°C
Adjustable Output Frequency Range	$f_{PLL0OSC}$		23	—	80	MHz
Lock Time	$t_{PLL0LOCK}$	f_{REF} = 20 MHz, $f_{PLL0OSC}$ = 80 MHz, M=24, N=99, LOCKTH = 0	—	1.7	—	µs
		f_{REF} = 32 kHz, $f_{PLL0OSC}$ = 80 MHz, M=0, N=2440, LOCKTH = 0	—	91	—	µs

***Note:** PLL0OSC in free-running oscillator mode.

Table 3.8. Internal Oscillators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
		T_A = 25 °C, V_{DD} = 3.3 V	19.5	20	20.5	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{DD} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{DD} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{DD} = 3.3 V	—	0.2	—	%/°C
RTC0 Oscillator (RTC0OSC)						
Missing Clock Detector Trigger Frequency	f_{RTCMCD}		—	8	15	kHz
RTC Robust Duty Cycle Range	DC_{RTC}		25	—	55	%
***Note:** PLL0OSC in free-running oscillator mode.						

Table 3.9. External Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Input CMOS Clock Frequency*	f_{CMOS}		0	—	50	MHz
External Input CMOS Clock High Time	t_{CMOSH}		9	—	—	ns
External Input CMOS Clock Low Time	t_{CMOSL}		9	—	—	ns
External Crystal Clock Frequency	f_{XTAL}		0.01	—	30	MHz
***Note:** Minimum of 10 kHz during debug operations.						

Table 3.15. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	760	—	mV
Offset Error*	E_{OFF}	T_A = 0 °C	—	±14	—	mV
Slope	M		—	2.8	—	mV/°C
Slope Error*	E_M		—	±120	—	µV/°C
Linearity			—	1	—	°C
Turn-on Time			—	1.8	—	µs
***Note:** Represents one standard deviation from the mean.						

Table 3.17. Port I/O (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Fall Time	t_F	Slew Rate Mode 0, V_{IOHD} = 5 V	—	50	—	ns
		Slew Rate Mode 1, V_{IOHD} = 5 V	—	300	—	ns
		Slew Rate Mode 2, V_{IOHD} = 5 V	—	1	—	µs
		Slew Rate Mode 3, V_{IOHD} = 5 V	—	3	—	µs
Input High Voltage	V_{IH}	1.8 V≤ V_{IOHD} ≤ 2.0 V	0.7 x V_{IOHD}	—	—	V
		2.0 V≤ V_{IOHD} ≤ 6 V	V_{IOHD} – 0.6	—	—	V
Input Low Voltage	V_{IL}		—	—	0.6	V
N-Channel Sink Current Limit (2.7 V ≤ V_{IOHD} ≤ 6 V, V_{OL} = 0.8 V) See Figure 3.1	I_{SINKL}	Mode 0	—	1.75	—	mA
		Mode 1	—	2.5	—	
		Mode 2	—	3.5	—	
		Mode 3	—	4.75	—	
		Mode 4	—	7	—	
		Mode 5	—	9.5	—	
		Mode 6	—	14	—	
		Mode 7	—	18.75	—	
		Mode 8	—	28.25	—	
		Mode 9	—	37.5	—	
		Mode 10	—	56.25	—	
		Mode 11	—	75	—	
		Mode 12	—	112.5	—	
		Mode 13	—	150	—	
		Mode 14	—	225	—	
		Mode 15	—	300	—	
Total N-Channel Sink Current on P4.0-P4.5 (DC)	I_{SINKLT}		—	—	400	mA

***Note:** $\overline{\text{RESET}}$ does not drive to logic high. Specifications for $\overline{\text{RESET}}$ V_{OL} adhere to the low drive setting.

3.2. Thermal Conditions

Table 3.18. Thermal Conditions

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Thermal Resistance*	θ_{JA}	LGA-92 Packages	—	35	—	°C/W
		TQFP-80 Packages	—	40	—	°C/W
		QFN-64 Packages	—	25	—	°C/W
		TQFP-64 Packages	—	30	—	°C/W
		QFN-40 Packages	—	30	—	°C/W
***Note:** Thermal resistance assumes a multi-layer PCB with any exposed pad soldered to a PCB pad.						

3.3. Absolute Maximum Ratings

Stresses above those listed under Table 3.19 may cause permanent damage to the device. This is a stress rating only and functional operation of the devices at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 3.19. Absolute Maximum Ratings

Parameter	Symbol	Test Condition	Min	Max	Unit
Ambient Temperature Under Bias	T_{BIAS}		–55	125	°C
Storage Temperature	T_{STG}		–65	150	°C
Voltage on VDD	V_{DD}		V_{SS}–0.3	4.2	V
Voltage on VREGIN	V_{REGIN}	EXTVREG0 Not Used	V_{SS}–0.3	6.0	V
		EXTVREG0 Used	V_{SS}–0.3	3.6	V
Voltage on VIO	V_{IO}		V_{SS}–0.3	4.2	V
Voltage on VIOHD	V_{IOHD}		V_{SS}–0.3	6.5	V
Voltage on I/O pins, non Port Bank 3 I/O	V_{IN}	$\overline{\text{RESET}}$, $V_{IO} \geq 3.3$ V	V_{SS}–0.3	5.8	V
		$\overline{\text{RESET}}$, $V_{IO} < 3.3$ V	V_{SS}–0.3	V_{IO}+2.5	V
		Port Bank 0, 1, and 2 I/O	V_{SS}–0.3	V_{IO}+0.3	V
		Port Bank 4 I/O	V_{SSHD}–0.3	V_{IOHD}+0.3	V
***Note:** VSS and VSSHD provide separate return current paths for device supplies, but are not isolated. They must always be connected to the same potential on board.					

Table 3.19. Absolute Maximum Ratings (Continued)

Parameter	Symbol	Test Condition	Min	Max	Unit
Voltage on I/O pins, Port Bank 3 I/O	V_{IN}	SiM3C1x7, PB3.0–PB3.7, $V_{IO} \geq 3.3$ V	V_{SS}–0.3	5.8	V
		SiM3C1x7, PB3.0–PB3.7, $V_{IO} < 3.3$ V	V_{SS}–0.3	V_{IO}+2.5	V
		SiM3C1x7, PB3.8 - PB3.11	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
		SiM3C1x6, PB3.0–PB3.5, $V_{IO} \geq 3.3$ V	V_{SS}–0.3	5.8	V
		SiM3C1x6, PB3.0–PB3.5, $V_{IO} < 3.3$ V	V_{SS}–0.3	V_{IO}+2.5	V
		SiM3C1x6, PB3.6–PB3.9	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
		SiM3C1x4, PB3.0–PB3.3	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
Total Current Sunk into Supply Pins	I_{SUPP}	V_{DD}, V_{REGIN}, V_{IO}, V_{IOHD}	—	400	mA
Total Current Sourced out of Ground Pins	I_{VSS}	V_{SS}, V_{SSHD}	400	—	mA
Current Sourced or Sunk by Any I/O Pin	I_{PIO}	PB0, PB1, PB2, PB3, and $\overline{\text{RESET}}$	–100	100	mA
		PB4	–300	300	mA
Current Injected on Any I/O Pin	I_{INJ}	PB0, PB1, PB2, PB3, and $\overline{\text{RESET}}$	–100	100	mA
		PB4	–300	300	mA
Total Injected Current on I/O Pins	ΣI_{INJ}	Sum of all I/O and $\overline{\text{RESET}}$	–400	400	mA

***Note:** VSS and VSSHD provide separate return current paths for device supplies, but are not isolated. They must always be connected to the same potential on board.

4.2. I/O

4.2.1. General Features

The SiM3C1xx ports have the following features:

- Push-pull or open-drain output modes and analog or digital modes.
- Option for high or low output drive strength.
- Port Match allows the device to recognize a change on a port pin value.
- Internal pull-up resistors are enabled or disabled on a port-by-port basis.
- Two external interrupts with up to 16 inputs provide monitoring capability for external signals.
- Internal Pulse Generator Timer (PB2 only) to generate simple square waves.
- A subset of pins can also serve as inputs to the Port Mapped Level Shifters available on the High Drive Pins.

4.2.2. High Drive Pins (PB4)

The High Drive pins have the following additional features:

- Programmable safe state: high, low, or high impedance.
- Programmable drive strength and slew rates.
- Programmable hardware current limiting.
- Powered from a separate source (VIOHD, which can be up to 6 V) from the rest of the device.
- Supports various functions, including GPIO, UART1 pins, EPCA0 pins, or Port Mapped Level Shifting.

4.2.3. 5 V Tolerant Pins (PB3)

The 5 V tolerant pins can be connected to external circuitry operating at voltages above the device supply without needing extra components to shift the voltage level.

4.2.4. Crossbars

The SiM3C1xx devices have two Crossbars with the following features:

- Flexible peripheral assignment to port pins.
- Pins can be individually skipped to move peripherals as needed for design or layout considerations.

The Crossbars have a fixed priority for each I/O function and assign these functions to the port pins. When a digital resource is selected, the least-significant unassigned port pin is assigned to that resource. If a port pin is assigned, the Crossbars skip that pin when assigning the next selected resource. Additionally, the Crossbars will skip port pins whose associated bits in the PBSKIPEN registers are set. This provides some flexibility when designing a system: pins involved with sensitive analog measurements can be moved away from digital I/O and peripherals can be moved around the chip as needed to ease layout constraints.

4.7.4. 16-Channel Capacitance-to-Digital Converter (CAPSENSE0)

The Capacitance Sensing module measures capacitance on external pins and converts it to a digital value. The CAPSENSE module has the following features:

- Multiple start-of-conversion sources (CSnTx).
- Option to convert to 12, 13, 14, or 16 bits.
- Automatic threshold comparison with programmable polarity (“less than or equal” or “greater than”).
- Four operation modes: single conversion, single scan, continuous single conversion, and continuous scan.
- Auto-accumulate mode that will take and average multiple samples together from a single start of conversion signal.
- Single bit retry options available to reduce the effect of noise during a conversion.
- Supports channel bonding to monitor multiple channels connected together with a single conversion.
- Scanning option allows the module to convert a single or series of channels and compare against the threshold while the AHB clock is stopped and the core is in a low power mode.

4.7.5. Low Current Comparators (CMP0, CMP1)

The Comparators take two analog input voltages and output the relationship between these voltages (less than or greater than) as a digital signal. The Low Power Comparator module includes the following features:

- Multiple sources for the positive and negative poles, including VDD, VREF, and 8 I/O pins.
- Two outputs are available: a digital synchronous latched output and a digital asynchronous raw output.
- Programmable hysteresis and response time.
- Falling or rising edge interrupt options on the comparator output.

4.7.6. Current-to-Voltage Converter (IVC0)

The IVC module provides inputs to the SARADCn modules so the input current can be measured. The IVC module has the following features:

- Two independent channels.
- Programmable input ranges (1–6 mA full-scale).

5. Ordering Information

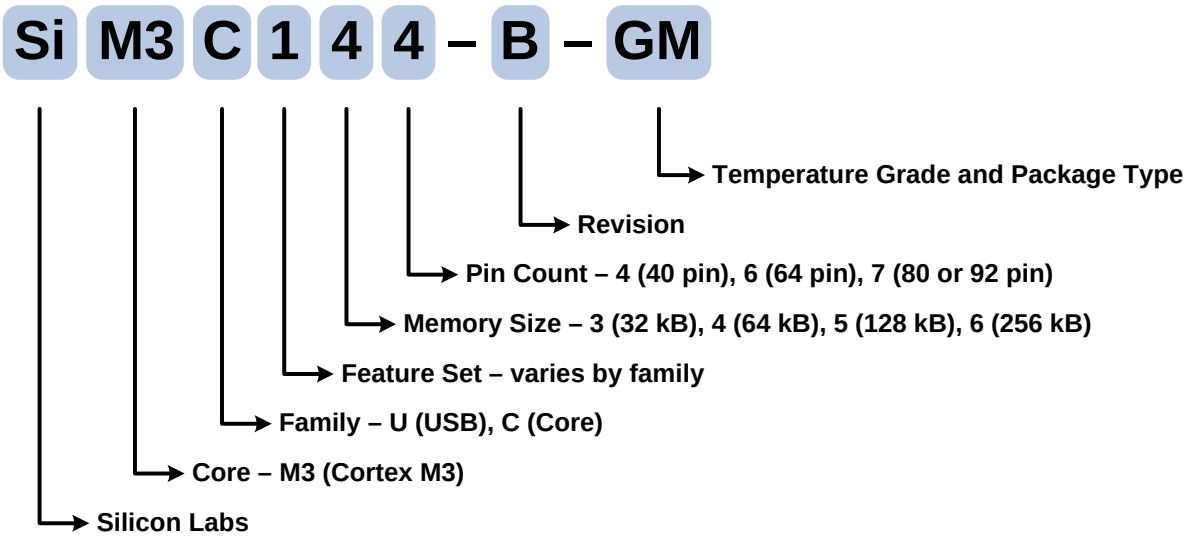

Figure 5.1. SiM3C1xx Part Numbering

All devices in the SiM3C1xx family have the following features:

- **Core:** ARM Cortex-M3 with maximum operating frequency of 80 MHz.
- **Flash Program Memory:** 32-256 kB, in-system programmable.
- **RAM:** 8–32 kB SRAM, with 4 kB retention SRAM
- **I/O:** Up to 65 multifunction I/O pins, including high-drive and 5 V-tolerant pins.
- **Clock Sources:** Internal and external oscillator options.
- **16-Channel DMA Controller.**
- **128/192/256-bit AES.**
- **16/32-bit CRC.**
- **Timers:** 2 x 32-bit (4 x 16-bit).
- **Real-Time Clock.**
- **Low-Power Timer.**
- **PCA:** 1 x 6 channels (Enhanced), 2 x 2 channels (Standard). PWM, capture, and clock generation capabilites.
- **ADC:** 2 x 12-bit 250 ksps (10-bit 1 Msps) SAR.
- **DAC:** 2 x 10-bit IDAC.
- **Temperature Sensor.**
- **Internal VREF.**
- **16-channel Capacitive Sensing (CAPSENSE).**
- **Comparator:** 2 x low current.
- **Current to Voltage Converter (IVC).**
- **Serial Buses:** 2 x USART, 2 x UART, 3 x SPI, 2 x I2C, 1 x I^2S.

The inclusion of some features varies across different members of the device family. The differences are detailed in Table 5.1.

Table 6.3. Pin Definitions and Alternate Functions for SiM3C1x4 (Continued)

Pin Name	Type	Pin Numbers	Crossbar Capability (see Port Config Section)	Port Match	Output Toggle Logic	External Trigger Inputs	Analog or Additional Functions
PB3.1	5 V Tolerant I/O	9	XBR1	✓		DAC0T1 DAC1T1 LPT0T1 INT0.1 INT1.1 WAKE.13	CMP0N.1 CMP1N.1 EXREGSN
PB3.2	5 V Tolerant I/O	8	XBR1	✓		DAC0T2 DAC1T2 LPT0T2 INT0.2 INT1.3 WAKE.14	CMP0P.2 CMP1P.2 EXREGOUT
PB3.3	5 V Tolerant I/O	7	XBR1	✓		DAC0T3 DAC1T3 INT0.3 INT1.3 WAKE.15	CMP0N.2 CMP1N.2 EXREGBD
PB4.0	High Drive I/O	6					
PB4.1	High Drive I/O	5					
PB4.2	High Drive I/O	4					
PB4.3	High Drive I/O	1					

6.4. LGA-92 Package Specifications

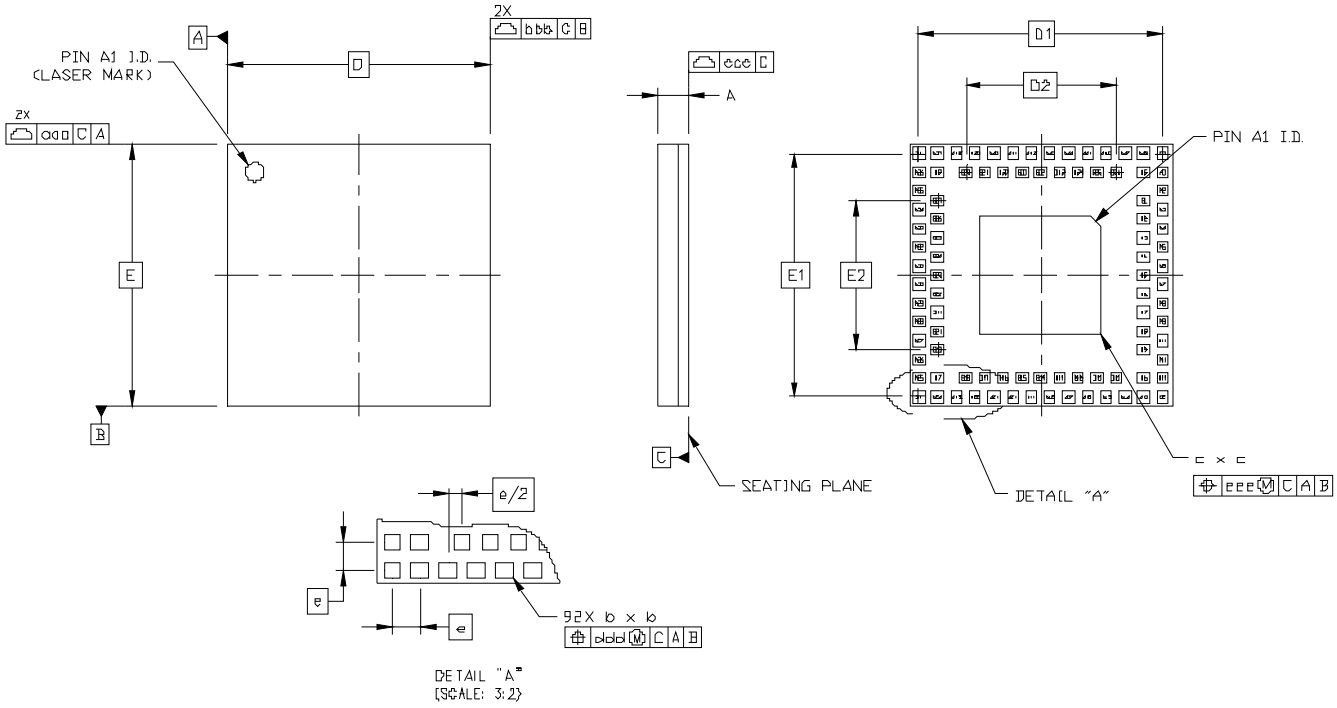

Figure 6.6. LGA-92 Package Drawing

Table 6.4. LGA-92 Package Dimensions

Dimension	Min	Nominal	Max
A	0.74	0.84	0.94
b	0.25	0.30	0.35
c	3.15	3.20	3.25
D		7.00 BSC	
D1		6.50 BSC	
D2		4.00 BSC	
e		0.50 BSC	
E		7.00 BSC	
E1		6.50 BSC	
E2		4.00 BSC	
aaa	—	—	0.10
bbb	—	—	0.10
ccc	—	—	0.08
ddd	—	—	0.10
eee	—	—	0.10

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

Table 6.6. TQFP-80 Package Dimensions (Continued)

Dimension	Min	Nominal	Max
L	0.45	0.60	0.75
L1		1.00 Ref	
Θ	0°	3.5°	7°
aaa		0.20	
bbb		0.20	
ccc		0.08	
ddd		0.08	
eee		0.05	

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MS-026, variant ADD.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

6.5.1. TQFP-80 Solder Mask Design

All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.

6.5.2. TQFP-80 Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 1:1 for all pads.

6.5.3. TQFP-80 Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6.7.1. TQFP-64 Solder Mask Design

All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.

6.7.2. TQFP-64 Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 1:1 for all pads.

6.7.3. TQFP-64 Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

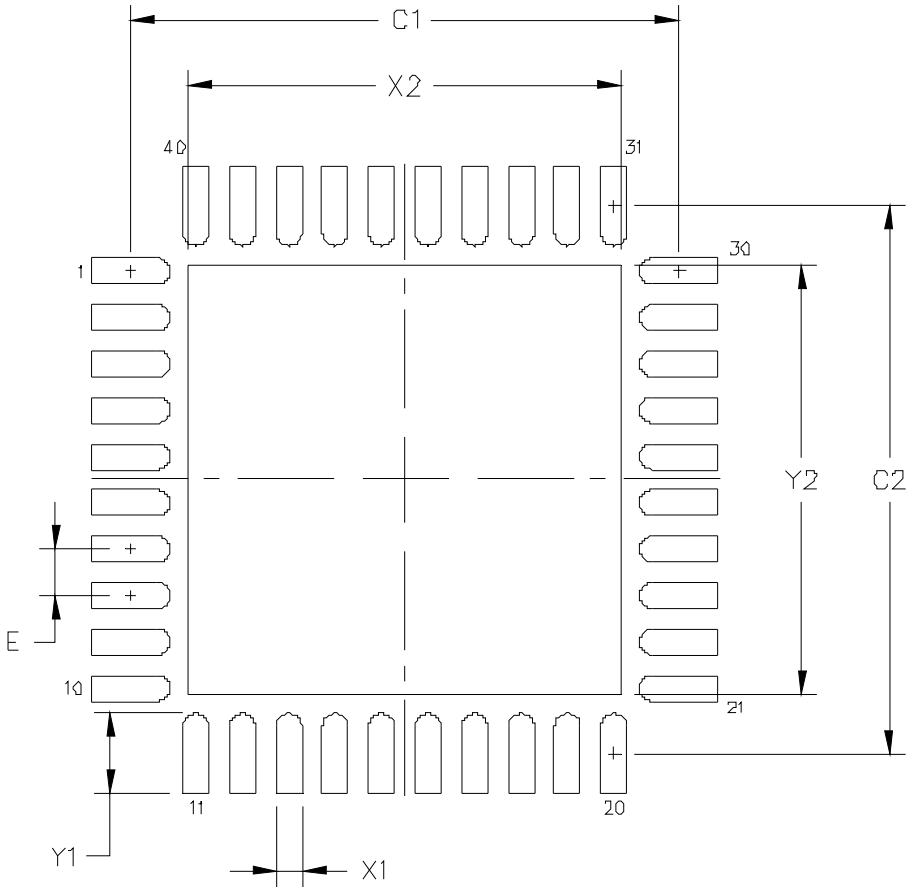

Figure 6.15. QFN-40 Landing Diagram

Table 6.13. QFN-40 Landing Diagram Dimensions

Dimension	mm
C1	5.90
C2	5.90
E	0.50
X1	0.30
Y1	0.85
X2	4.65
Y2	4.65

Notes:
1. All dimensions shown are in millimeters (mm).
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05 mm.

7. Revision Specific Behavior

This chapter details any known differences from behavior as stated in the device datasheet and reference manual. All known errata for the current silicon revision are rolled into this section at the time of publication. Any errata found after publication of this document will initially be detailed in a separate errata document until this datasheet is revised.

7.1. Revision Identification

The Lot ID Code on the top side of the device package can be used for decoding device revision information. Figures 7.1, 7.2, 7.3, and 7.4 show how to find the Lot ID Code on the top side of the device package.

In addition, firmware can determine the revision of the device by checking the DEVICEID registers.

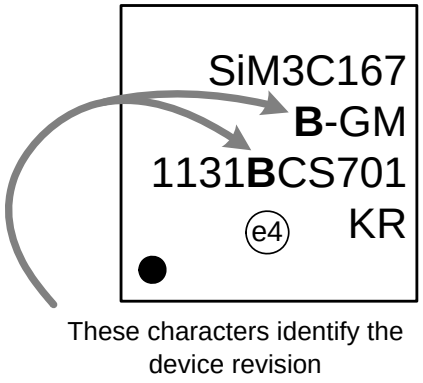

Figure 7.1. LGA-92 SiM3C1x7 Revision Information

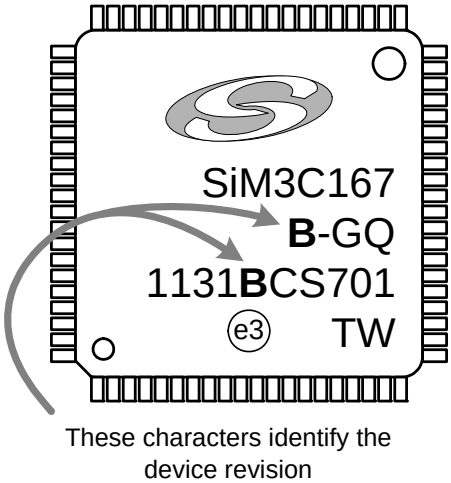

Figure 7.2. TQFP-80 SiM3C1x7 Revision Information